

# NSL35TT1

## High Current Surface Mount PNP Silicon Low $V_{CE(sat)}$ Transistor for Battery Operated Applications



ON Semiconductor™

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**35 VOLTS  
1.0 AMPS  
PNP TRANSISTOR**

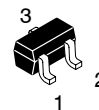
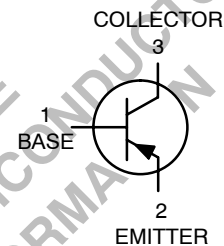
### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	$V_{CEO}$	-35	Vdc
Collector-Base Voltage	$V_{CBO}$	-50	Vdc
Emitter-Base Voltage	$V_{EBO}$	-5.0	Vdc
Collector Current – Peak – Continuous	$I_C$	-1.0 -500	Adc mAdc
Electrostatic Discharge	ESD	HBM Class 3B MM Class C	

### THERMAL CHARACTERISTICS

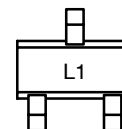
Characteristic	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 1)	210 1.7	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 1)	595	°C/W
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$ (Note 2)	365 2.9	mW mW/°C
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$ (Note 2)	340	°C/W
Thermal Resistance, Junction to Lead #3	$R_{\theta JL}$	205	°C/W
Junction and Storage Temperature Range	$T_J, T_{stg}$	-55 to +150	°C

1. FR-4 @ Minimum Pad
2. FR-4 @ 1.0 X 1.0 inch Pad



**CASE 463  
SOT-416/SC-75  
STYLE 1**

### DEVICE MARKING



L1 = Specific Device Code

### ORDERING INFORMATION

Device	Package	Shipping
NSL35TT1	SOT-416	3000/Tape & Reel

# NSL35TT1

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typical	Max	Unit
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### OFF CHARACTERISTICS

Collector – Emitter Breakdown Voltage ( $I_C = -10 \text{ mAdc}$ , $I_B = 0$ )	$V_{(BR)CEO}$	-35	-45	-	Vdc
Collector – Base Breakdown Voltage ( $I_C = -0.1 \text{ mAdc}$ , $I_E = 0$ )	$V_{(BR)CBO}$	-50	-65	-	Vdc
Emitter – Base Breakdown Voltage ( $I_E = -0.1 \text{ mAdc}$ , $I_C = 0$ )	$V_{(BR)EBO}$	-5.0	-7.0	-	Vdc
Collector Cutoff Current ( $V_{CB} = -35 \text{ Vdc}$ , $I_E = 0$ )	$I_{CBO}$	-	-0.03	-0.1	$\mu\text{Adc}$
Collector – Emitter Cutoff Current ( $V_{CES} = -30 \text{ Vdc}$ )	$I_{CES}$	-	-0.03	-0.1	$\mu\text{Adc}$
Emitter Cutoff Current ( $V_{EB} = -4.0 \text{ Vdc}$ )	$I_{EBO}$	-	-0.01	-0.1	$\mu\text{Adc}$

### ON CHARACTERISTICS

DC Current Gain (Note 3) ( $I_C = -100 \text{ mA}$ , $V_{CE} = -1.0 \text{ V}$ ) ( $I_C = -100 \text{ mA}$ , $V_{CE} = -2.0 \text{ V}$ ) ( $I_C = -250 \text{ mA}$ , $V_{CE} = -2.0 \text{ V}$ )	$h_{FE}$	100 100 100	180 180 150	- - -	
Collector – Emitter Saturation Voltage (Note 3) ( $I_C = -50 \text{ mA}$ , $I_B = -0.5 \text{ mA}$ ) ( $I_C = -100 \text{ mA}$ , $I_B = -1.0 \text{ mA}$ ) ( $I_C = -250 \text{ mA}$ , $I_B = -2.5 \text{ mA}$ ) ( $I_C = -250 \text{ mA}$ , $I_B = -5.0 \text{ mA}$ ) ( $I_C = -500 \text{ mA}$ , $I_B = -50 \text{ mA}$ )	$V_{CE(sat)}$	- - - - -	-0.090 -0.200 -0.320 -0.170 -0.270	-0.130 -0.350 -0.450 - -0.350	V
Base – Emitter Saturation Voltage (Note 3) ( $I_C = -150 \text{ mA}$ , $I_B = -20 \text{ mA}$ )	$V_{BE(sat)}$	-	-0.81	-0.9	V
Base – Emitter Turn-on Voltage (Note 3) ( $I_C = -150 \text{ mA}$ , $V_{CE} = -3.0 \text{ V}$ )	$V_{BE(on)}$	-	-0.81	-0.875	V
Input Capacitance ( $V_{EB} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$ )	$C_{ibo}$	-	45	-	pF
Output Capacitance ( $V_{CB} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$ )	$C_{obo}$	-	18	-	pF
Turn-On Time ( $I_{B1} = -50 \text{ mA}$ , $I_C = -500 \text{ mA}$ , $R_L = 3.0 \Omega$ )	$t_{on}$	-	40	-	ns
Turn-Off Time ( $I_{B1} = I_{B2} = -50 \text{ mA}$ , $I_C = -500 \text{ mA}$ , $R_L = 3.0 \Omega$ )	$t_{off}$	-	70	-	ns

3. Pulsed Condition: Pulse Width = 300  $\mu\text{sec}$ , Duty Cycle  $\leq 2\%$

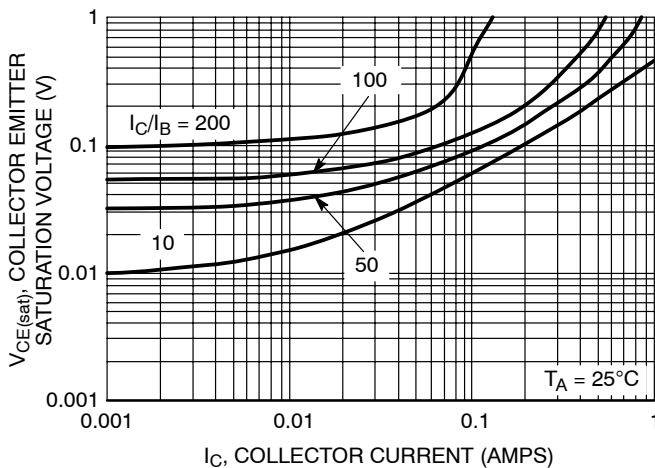


Figure 1. Collector Emitter Saturation Voltage vs. Collector Current

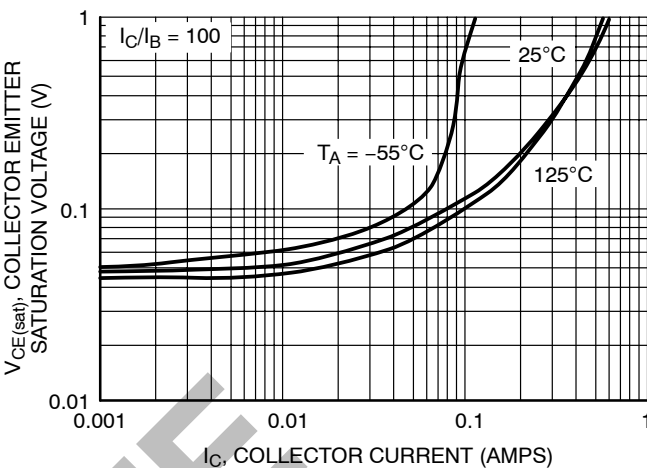


Figure 2. Collector Emitter Saturation Voltage vs. Collector Current

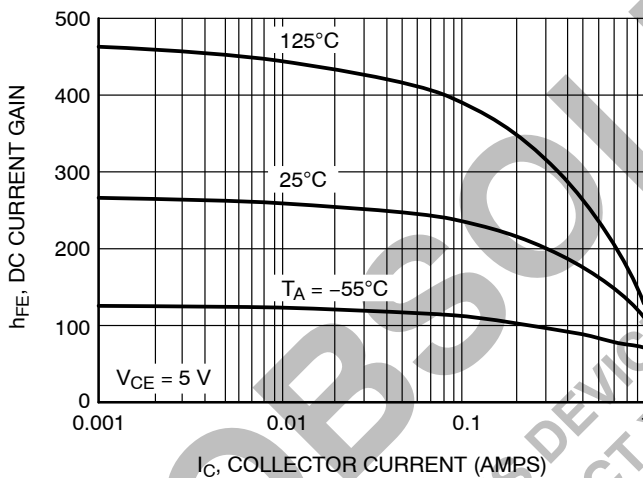


Figure 3. DC Current Gain

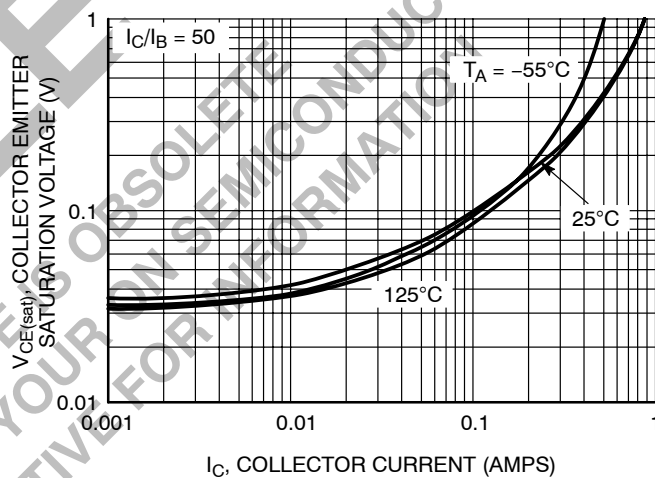


Figure 4. Collector Emitter Saturation Voltage vs. Collector Current

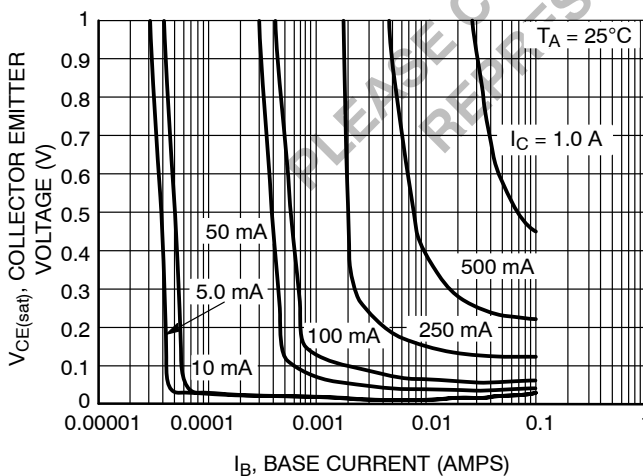


Figure 5. Collector Emitter Saturation Voltage vs. Base Current

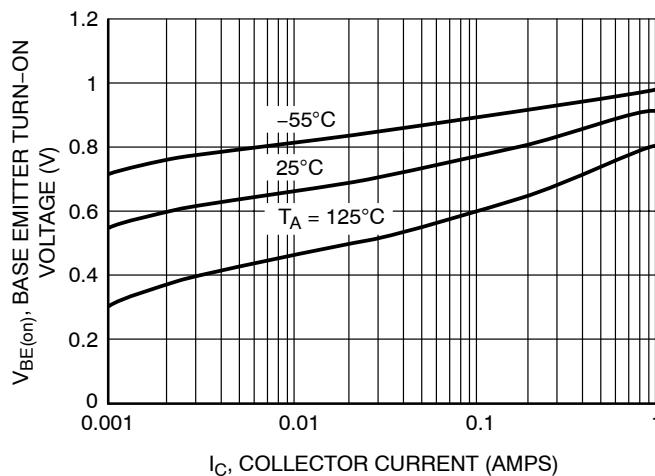
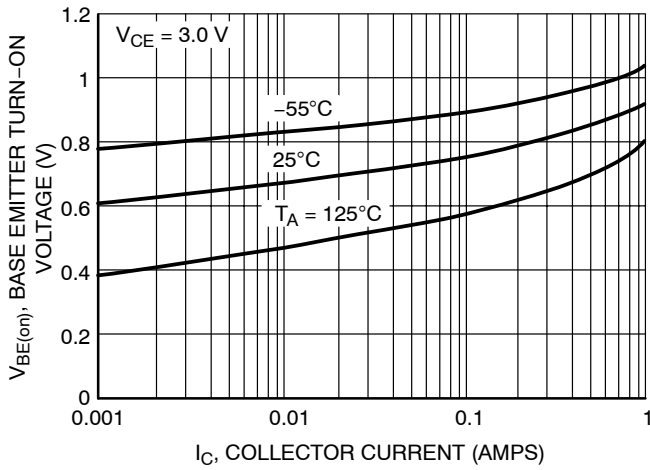
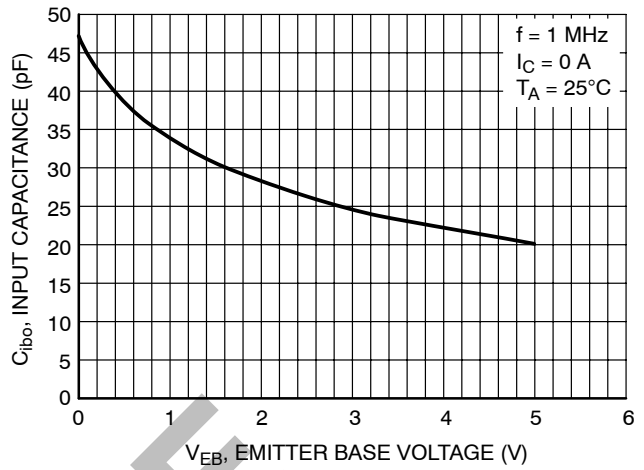


Figure 6. Base Emitter Saturation Voltage vs. Collector Current

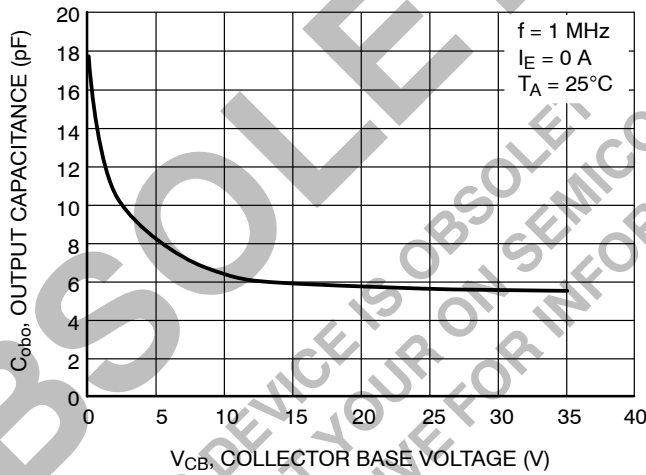
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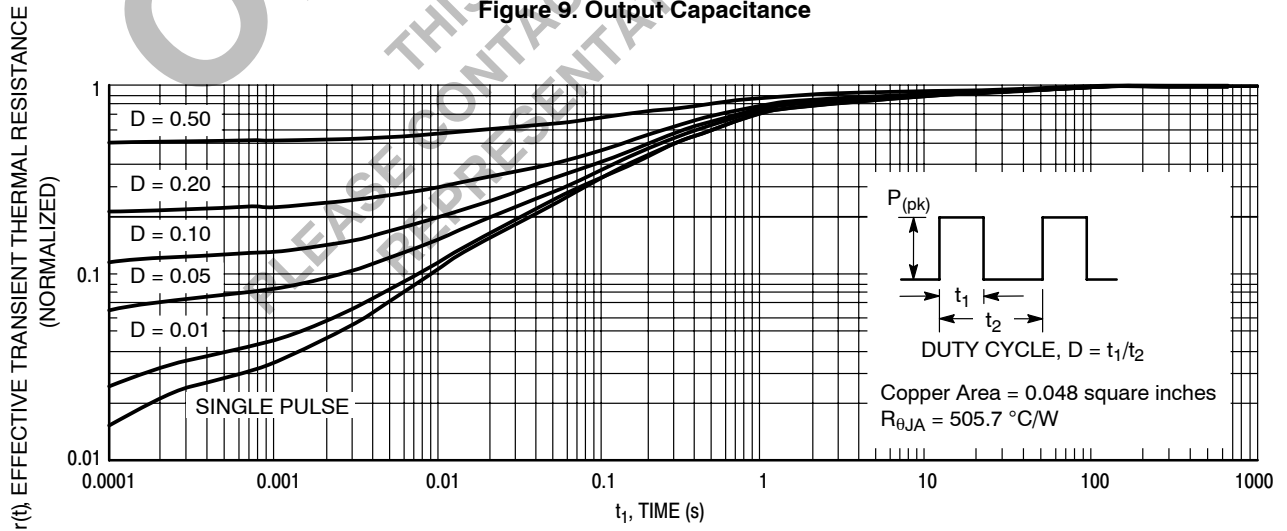
**Figure 7. Base Emitter Turn-On Voltage vs. Collector Current**



**Figure 8. Input Capacitance**



**Figure 9. Output Capacitance**



**Figure 10. Normalized Thermal Response**



## SOLDER STENCIL GUIDELINES

Prior to placing surface mount components onto a printed circuit board, solder paste must be applied to the pads. A solder stencil is required to screen the optimum amount of solder paste onto the footprint. The stencil is made of brass or stainless steel with a typical thickness of 0.008 inches.

The stencil opening size for the surface mounted package should be the same as the pad size on the printed circuit board, i.e., a 1:1 registration.

## TYPICAL SOLDER HEATING PROFILE

For any given circuit board, there will be a group of control settings that will give the desired heat pattern. The operator must set temperatures for several heating zones, and a figure for belt speed. Taken together, these control settings make up a heating “profile” for that particular circuit board. On machines controlled by a computer, the computer remembers these profiles from one operating session to the next. Figure 11 shows a typical heating profile for use when soldering a surface mount device to a printed circuit board. This profile will vary among soldering systems but it is a good starting point. Factors that can affect the profile include the type of soldering system in use, density and types of components on the board, type of solder used, and the type of board or substrate material being used. This profile shows temperature versus time.

The line on the graph shows the actual temperature that might be experienced on the surface of a test board at or near a central solder joint. The two profiles are based on a high density and a low density board. The Vitronics SMD310 convection/infrared reflow soldering system was used to generate this profile. The type of solder used was 62/36/2 Tin Lead Silver with a melting point between 177–189°C. When this type of furnace is used for solder reflow work, the circuit boards and solder joints tend to heat first. The components on the board are then heated by conduction. The circuit board, because it has a large surface area, absorbs the thermal energy more efficiently, then distributes this energy to the components. Because of this effect, the main body of a component may be up to 30 degrees cooler than the adjacent solder joints.

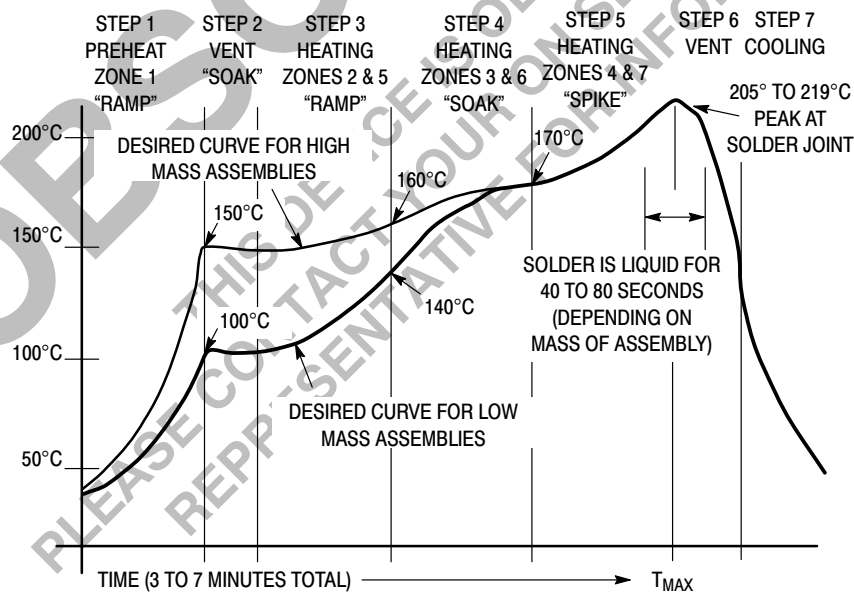
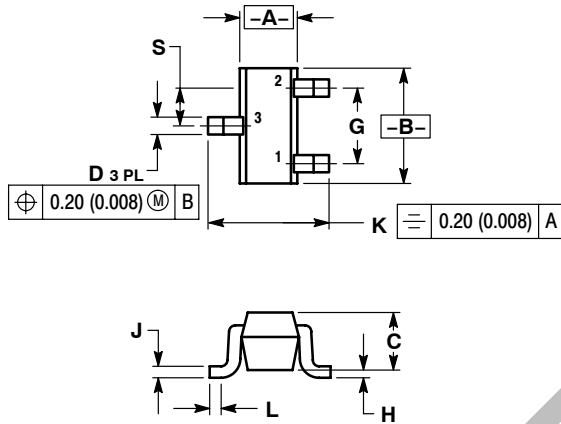


Figure 11. Typical Solder Heating Profile

# NSL35TT1

## PACKAGE DIMENSIONS

SC-75/SOT-416  
CASE 463-01  
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.70	0.80	0.028	0.031
B	1.40	1.80	0.055	0.071
C	0.60	0.90	0.024	0.035
D	0.15	0.30	0.006	0.012
G	1.00 BSC		0.039 BSC	
H	---	0.10	---	0.004
J	0.10	0.25	0.004	0.010
K	1.45	1.75	0.057	0.069
L	0.10	0.20	0.004	0.008
S	0.50 BSC		0.020 BSC	

- STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

OBSOLETE

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